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Vishay Siliconix

Automotive N-Channel 30 V (D-S) 175 °C MOSFET

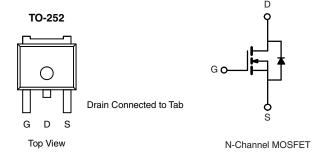
PRODUCT SUMMARY				
V _{DS} (V)	30			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0032			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0039			
I _D (A)	100			
Configuration	Single			

FEATURES

- TrenchFET® Power MOSFET
- 100 % R_g and UIS Tested
- AEC-Q101 Qualifiedd
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912



FREE



ORDERING INFORMATION				
Package	TO-252			
Lead (Pb)-free and Halogen-free	SQD100N03-3m2L-GE3			

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	30	.,,	
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Drain Current ^a	T _C = 25 °C	1	100		
	T _C = 125 °C	l _D	89		
Continuous Source Current (Diode Conduction) ^a		Is	100	Α	
Pulsed Drain Current ^b		I _{DM}	150		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	60		
Single Pulse Avalanche Energy	L = 0.1 IIII	E _{AS}	180	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	0	136	W	
	T _C = 125 °C	P _D	45		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	50	°C/W
Junction-to-Case (Drain)		R_{thJC}	1.1	C/ VV

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static				1				
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		30	-	-	.,	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		2.0	2.5	V	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA	
		V _{GS} = 0 V	V _{DS} = 30 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 30 V, T _J = 125 °C	-		50	μA	
		V _{GS} = 0 V	V _{DS} = 30 V, T _J = 175 °C	-		150		
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	50	-	-	Α	
		V _{GS} = 10 V	I _D = 20 A	-	0.0027	0.0032	Ω	
Drain-Source On-State Resistance ^a	В	V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.0049		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-		0.0058		
		V _{GS} = 4.5 V	I _D = 15 A	-	0.0031	0.0039		
Forward Transconductanceb	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		-	122	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}			-	5053	6316	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{DS} = 15 V, f = 1 MHz	-	921	1151		
Reverse Transfer Capacitance	C _{rss}]		-	377	471		
Total Gate Charge ^c	Qg			-	77	116		
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 15 \text{ V}, I_{D} = 50 \text{ A}$	-	14.3	-	nC	
Gate-Drain Charge ^c	Q _{gd}	1			11	-		
Gate Resistance	R _g	f = 1 MHz		1.14	2.28	3.42	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	10	15		
Rise Time ^c	t _r	$V_{DD} = 15 \text{ V}, \text{ R}_L = 0.3 \Omega$ $I_D \cong 50 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega$		-	10	15	ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	42	63		
Fall Time ^c	t _f			-	10	15		
Source-Drain Diode Ratings and Chara	acteristics ^b							
Pulsed Current ^a	I _{SM}			-	_	150	Α	
Forward Voltage	V_{SD}	I _F = 40 A, V _{GS} = 0 V		İ	0.85	1.2	V	

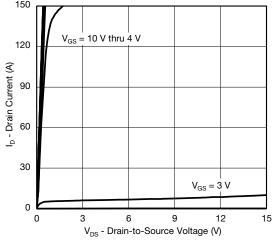
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

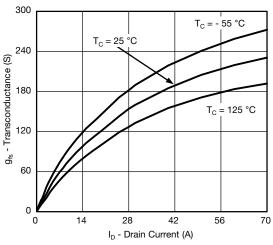
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



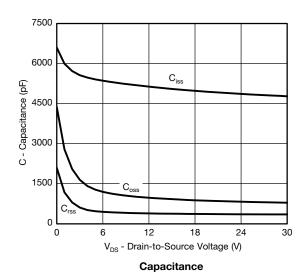
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

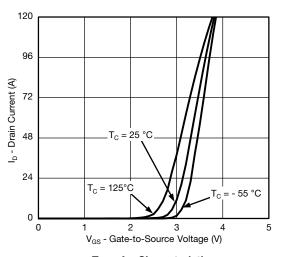


Output Characteristics

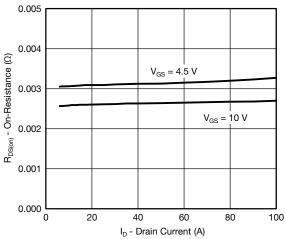


Transconductance

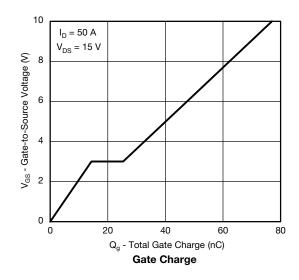




Transfer Characteristics

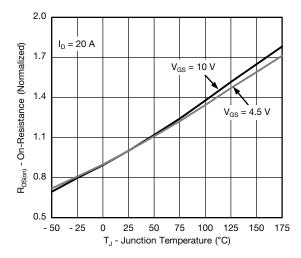


On-Resistance vs. Drain Current

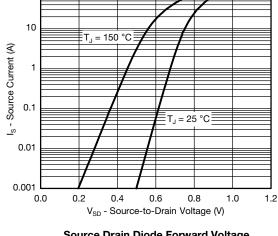




TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

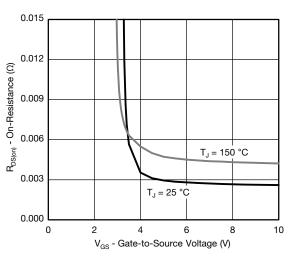


On-Resistance vs. Junction Temperature

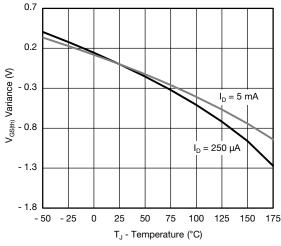


100

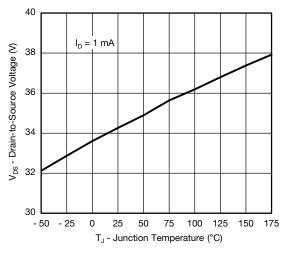
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



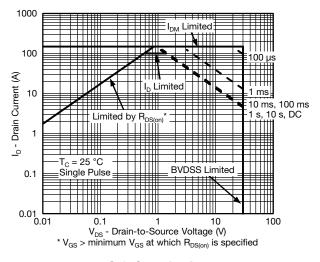
Threshold Voltage



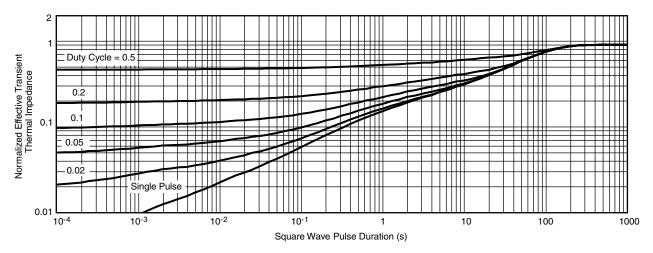
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



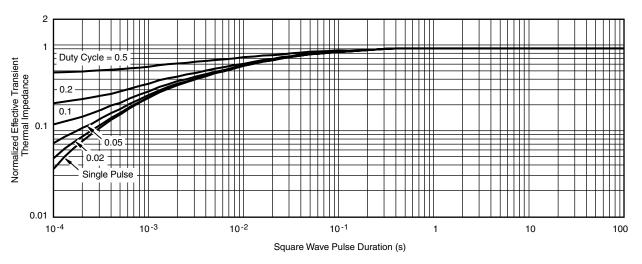
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

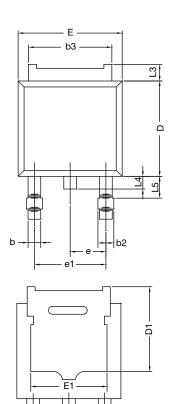
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

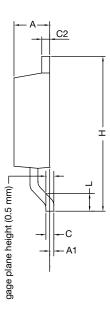
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg262573.



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TO-252AA Case Outline





	MILLIN	METERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
E	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090 BSC		
e1	4.56 BSC		0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0592-Rev. A, 02-Sep-13 DWG: 6019					

Note

• Dimension L3 is for reference only.

Revision: 02-Sep-13 Document Number: 64424



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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